AMENDMENT TO THE CLAIMS

Please cancel claims 25-26 without prejudice or disclaimer of their underlying subject matter.

1-30. (Canceled)

31. (Previously presented) A mask fabrication method comprising the steps of:

acquiring input data, said graphic input data corresponding to an LSI pattern to be formed on a wafer;

dividing said graphic input data into V-line data and H-line data, said V-line data being said input data extending onto said wafer in a first direction and said H-line data being said input data extending onto said wafer in a direction other than said first direction;

forming a V-line reflective mask adapted to reflect a light onto said wafer, a mask pattern for said V-line reflective mask consisting only of V-line pattern forming elements; and

forming an H-line reflective mask adapted to reflect said light onto said wafer, a mask pattern for said H-line reflective mask consisting only of H-line pattern forming elements,

wherein said light is projected along a projection vector in a projection direction,

wherein said first direction is alignable in said projection direction, and

wherein said direction other than said first direction is alignable in said projection direction.

32. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said V-line data correspond to said V-line pattern forming elements and said H-line data correspond to said H-line pattern forming elements.

33. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said light incident to said V-line reflective mask is skewed from normal of a reflective plane for said V-line reflective mask.

34. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said light incident to said H-line reflective mask is skewed from normal of a reflective plane for said H-line reflective mask.

35. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said light reflected from said V-line pattern forming elements is adapted to extend onto said wafer in said first direction.

36. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said light reflected from said H-line pattern forming elements is adapted to extend onto said wafer in said direction other than said first direction.

37. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said mask pattern for said V-line reflective mask consists only of said V-line pattern forming elements.

38. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said mask pattern for said H-line reflective mask consists only of said H-line pattern forming elements.

39. (Previously presented) The mask fabrication method as cited in Claim 31, further comprising:

forming an absorption film on said V-line reflective mask, said absorption film being adapted to absorb said light.

40. (Previously presented) The mask fabrication method as cited in Claim 31, further comprising:

forming an absorption film on said H-line reflective mask, said absorption film being adapted to absorb said light.

41. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said light is from the group consisting of a charged particle beam, an x-ray, an extreme ultra violet ray, an ultra violet ray, and a visible light.

42. (Previously presented) The mask fabrication method as cited in Claim 31, wherein said charged particle beam is one of an electron beam and an ion beam.